

**TrenchT4™**  
**Power MOSFET**
**IXTT440N04T4HV**

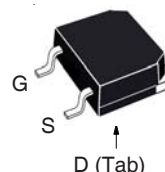
$$V_{DSS} = 40V$$

$$I_{D25} = 440A$$

$$R_{DS(on)} \leq 1.25m\Omega$$

 N-Channel Enhancement Mode  
 Avalanche Rated


TO-268HV


 G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$	40	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$	40	V
$V_{GSM}$	Transient	$\pm 15$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	440	A
$I_{LRMS}$	Lead Current Limit, RMS	160	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	1200	A
$I_A$	$T_C = 25^\circ\text{C}$	440	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.5	J
$P_D$	$T_C = 25^\circ\text{C}$	940	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +175	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
<b>Weight</b>		4	g

**Features**

- International Standard Package
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	40		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			10 $\mu A$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 100A$ , Note 1			1.25 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	110	180	S
$R_{Gi}$	Gate Input Resistance		1.1	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		26	nF
$C_{oss}$			3570	pF
$C_{rss}$			235	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		44	ns
$t_r$			250	ns
$t_{d(off)}$			120	ns
$t_f$			74	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		480	nC
$Q_{gs}$			136	nC
$Q_{gd}$			162	nC
$R_{thJC}$				0.16 $^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			440 A
$I_{SM}$	Repetitive, pulse Width Limited by $T_{JM}$			1760 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 150\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 30\text{V}$		72	ns
$Q_{RM}$			110	nC
$I_{RM}$			3	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

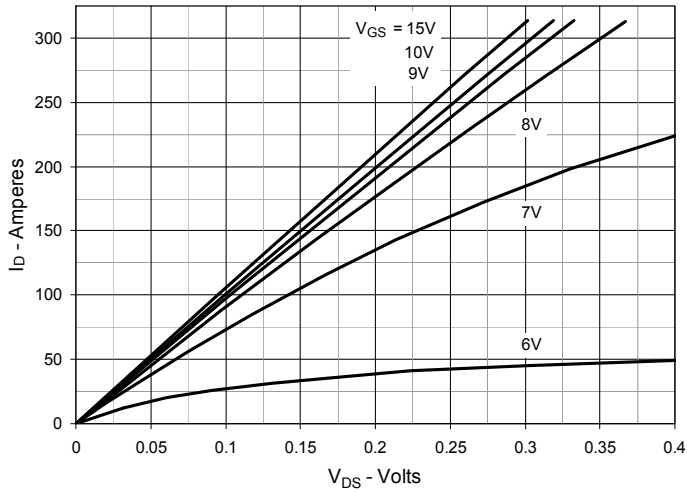
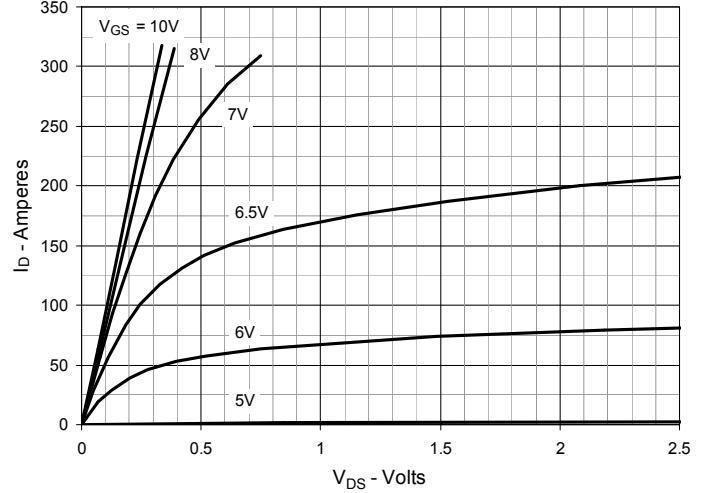
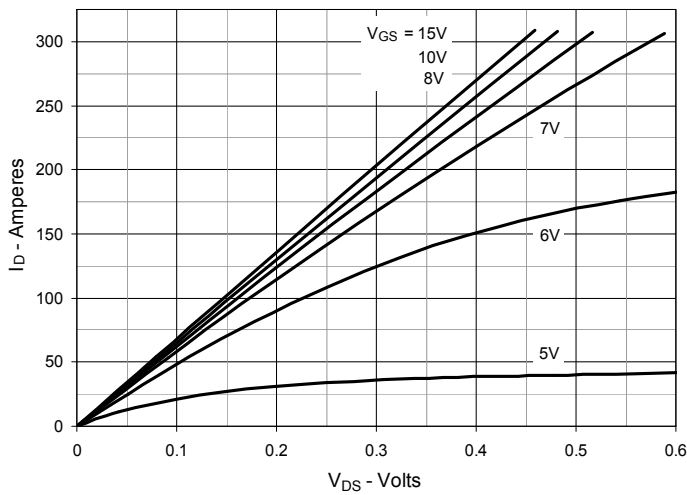
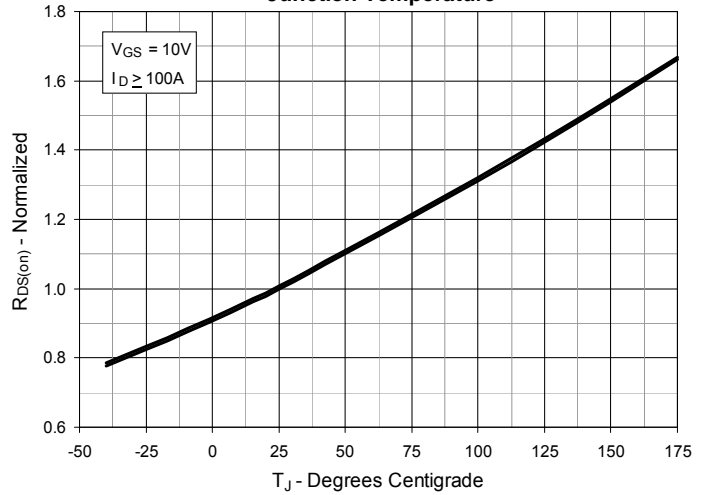
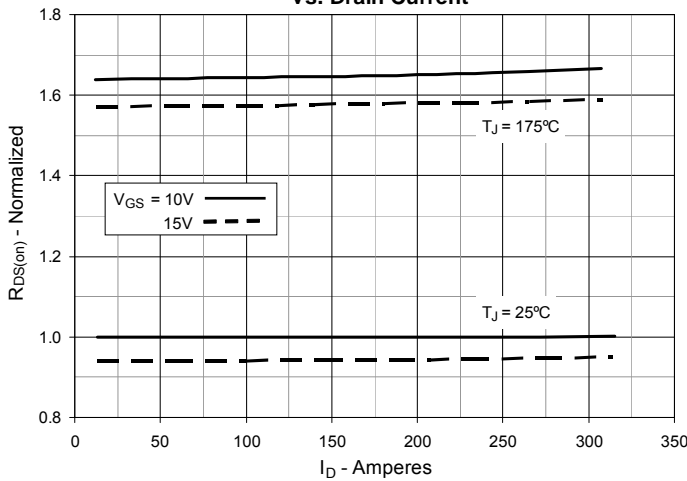
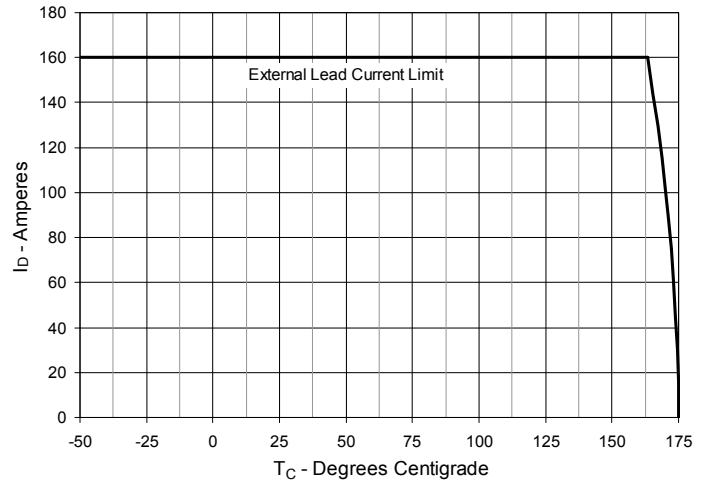
**ADVANCE TECHNICAL INFORMATION**

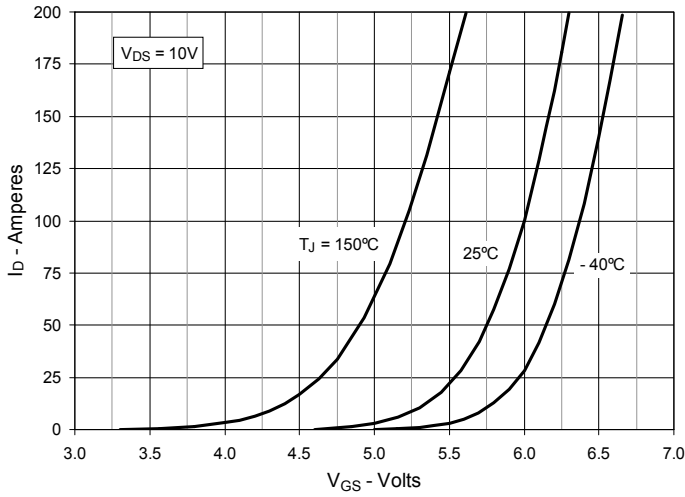
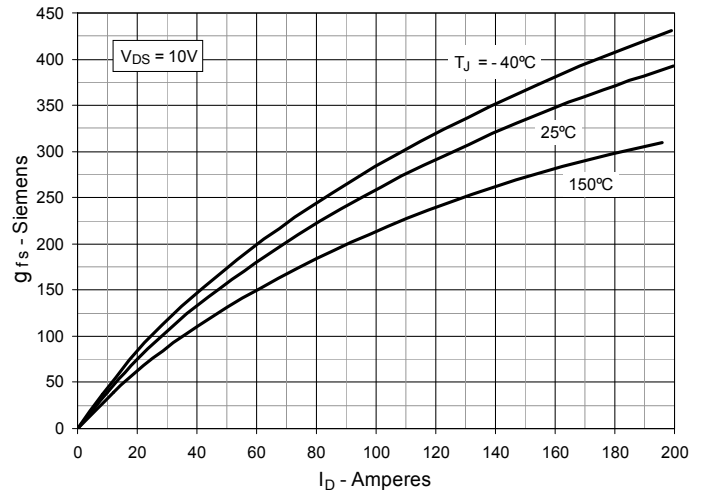
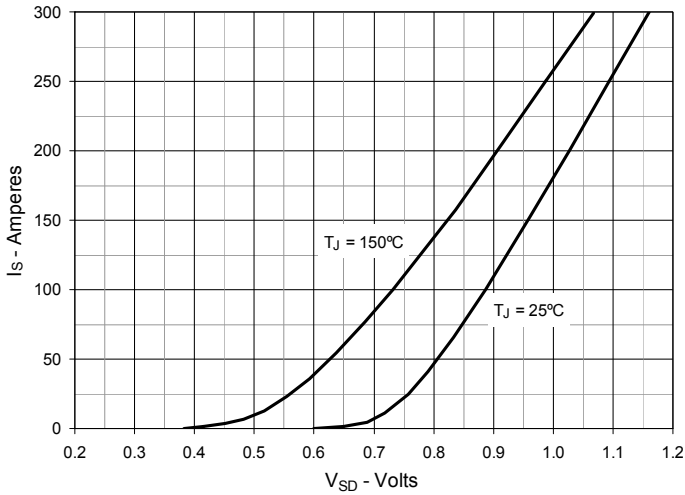
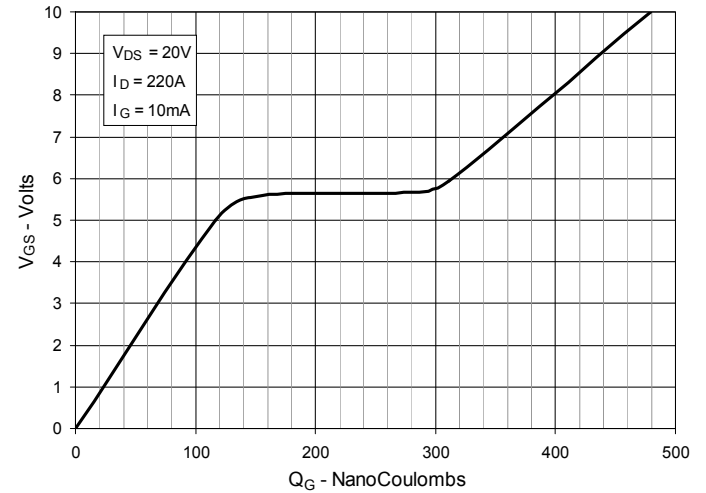
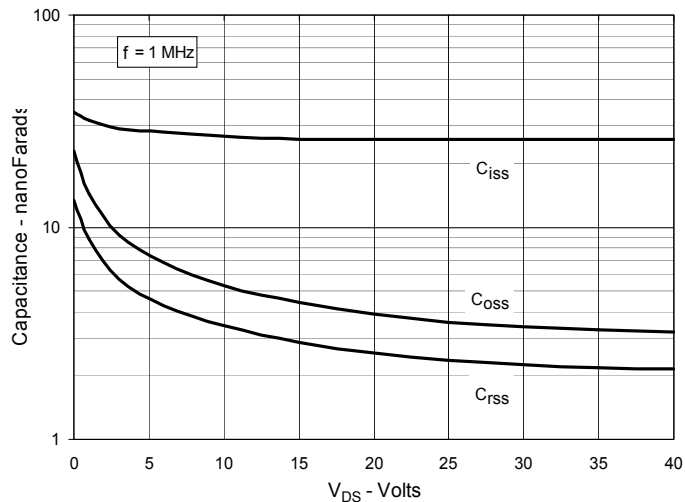
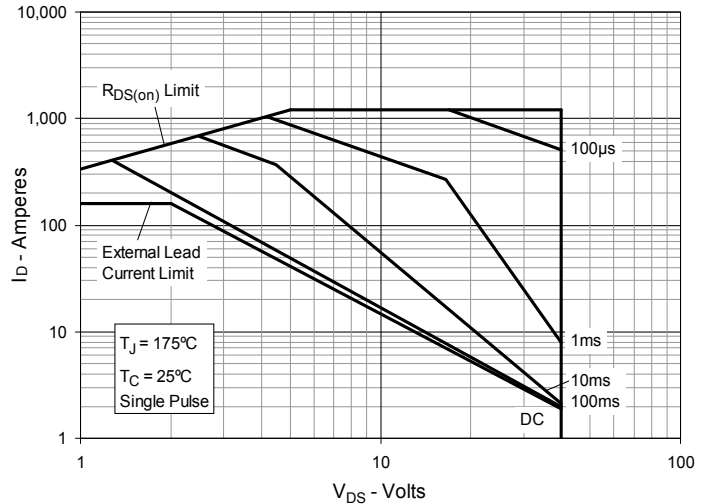
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

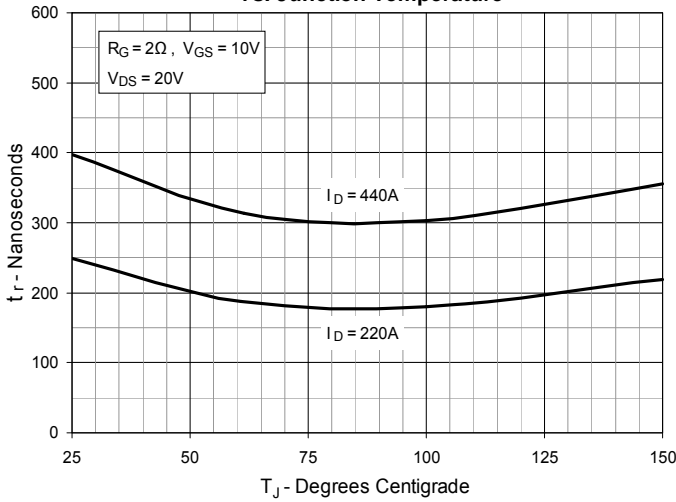
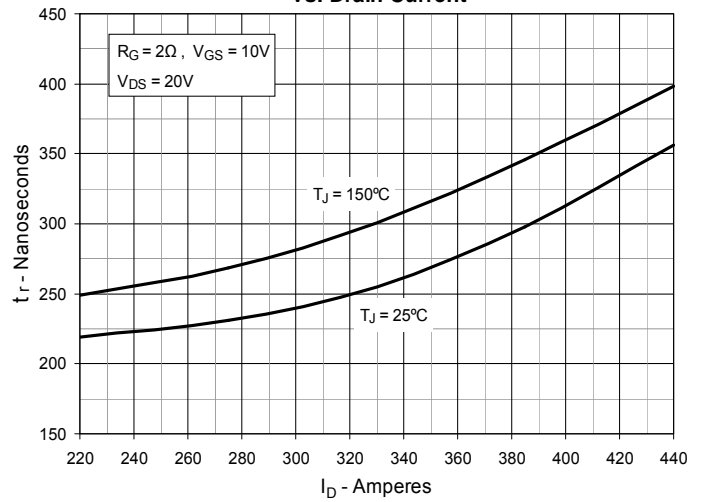
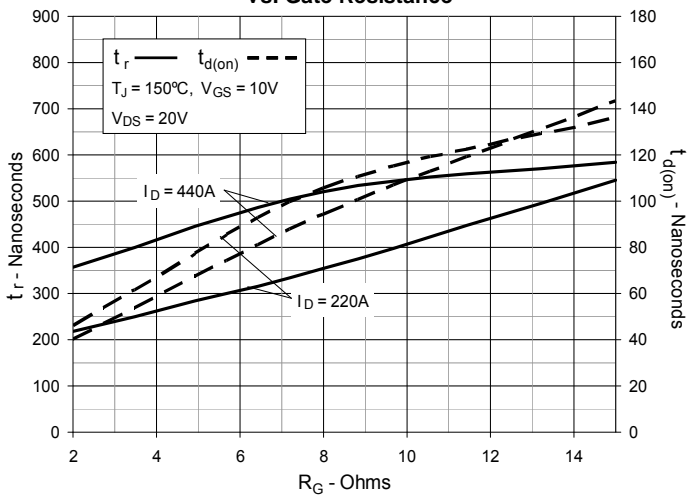
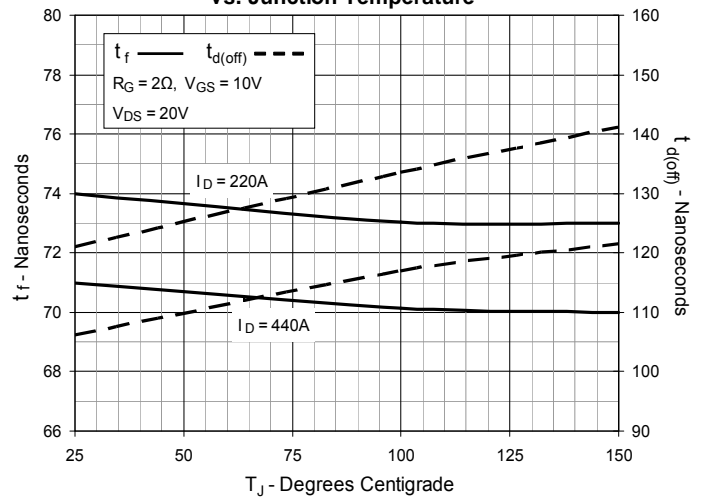
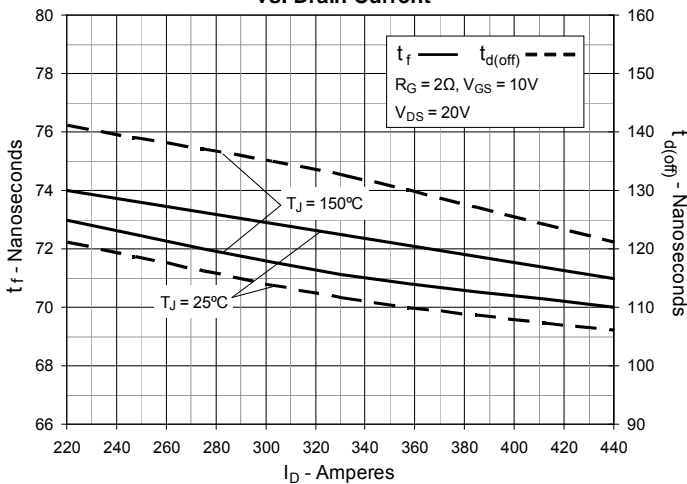
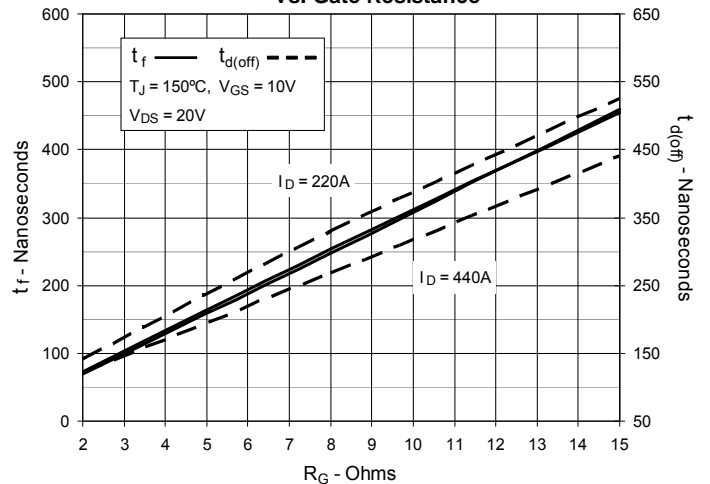
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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

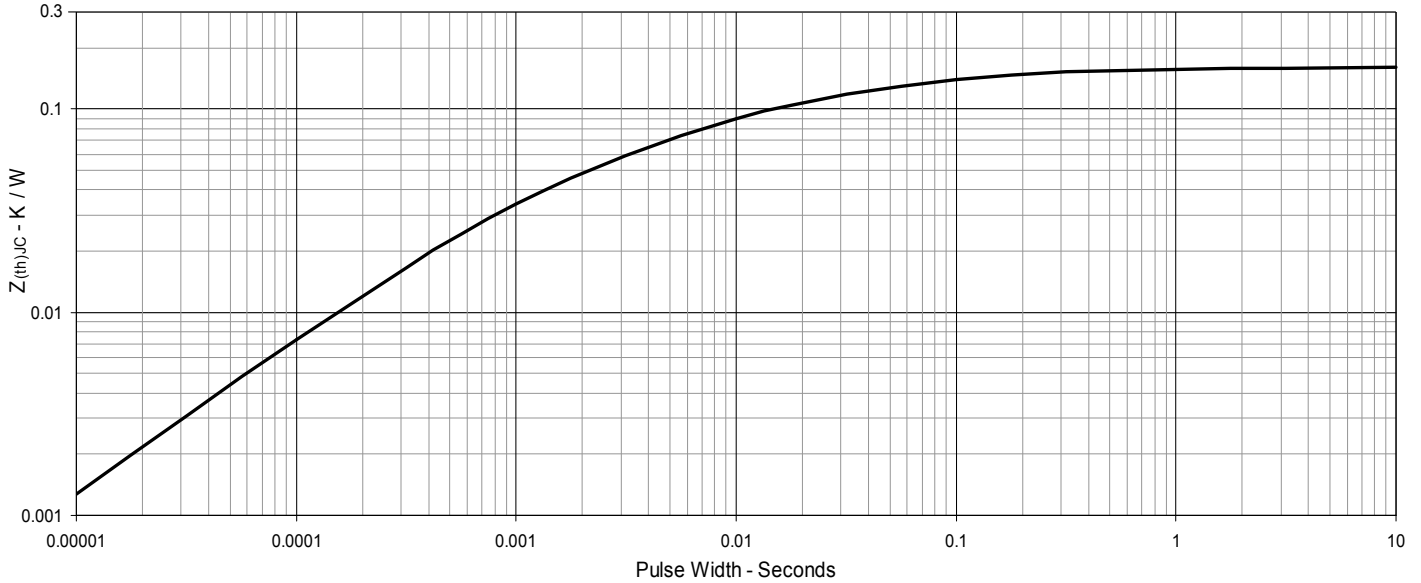
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4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$** 

**Fig. 4. Normalized  $R_{DS(on)}$  to  $I_D = 100\text{A}$  Value vs. Junction Temperature**

**Fig. 5. Normalized  $R_{DS(on)}$  to  $I_D = 100\text{A}$  vs. Drain Current**

**Fig. 6. Drain Current vs. Case Temperature**


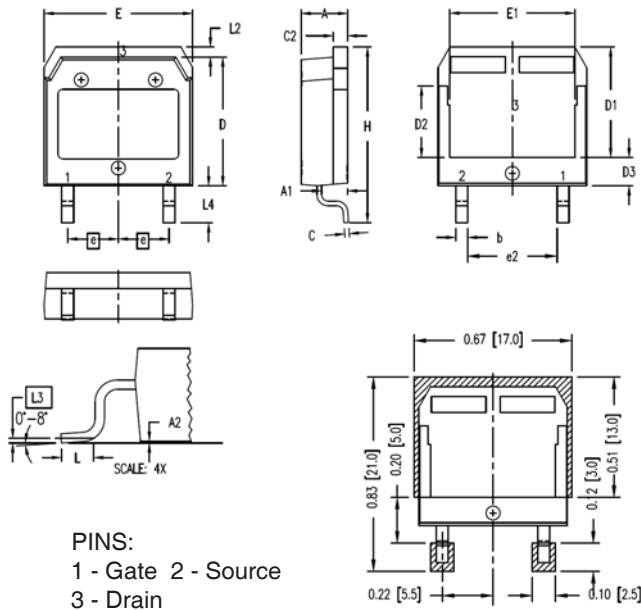
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**

**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**

**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**

**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**

**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**

**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**


**Fig. 19. Maximum Transient Thermal Impedance**



**TO-268HV Outline**



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10